

<b>Crystal Properties</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Crystalline structure	-	Monocrystalline	
Growth technique	-	Czochralski (Cz)	
Orientation	-	<100> ±1°	
Slice orientation	Degrees	ON ±1.0°	
<b>Electrical Properties</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Conductance type	-	P-type	
Dopant	-	Boron	
Resistivity	Ω-cm	1 - 100	
<b>Geometrical Properties</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Diameter	mm	200±0.2	
Thickness	μm	725±25	
TTV	μm	≤5	
Warp	μm	≤40	
Bow	μm	≤40	
Notch	-	SEMI standard	
Notch depth	mm	1.0 + 0.25 – 0.00	
Notch angle	-	90° +5° -1°	
Notch orientation	-	<110> ±1°	
<b>Surface Appearance</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Front surface	-	Polished	
Back surface	-	Polished	
Frontside particles ≥0.20 μm (LPD)	No./wafer	≤30	
Nominal edge exclusion	mm	3.0	
<b>Wafer Identification</b>			
<b>PARAMETER</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Lasermark	-	None	
<b>Surface Metals</b>			
<b>APPLICABLE METALS</b>	<b>UNITS</b>	<b>SPECIFICATION</b>	<b>NOTE</b>
Al, Ca, Cl, Cr, Cu, Fe, K, Na, Ni, Zn	Atoms/cm <sub>2</sub>	≤5E10	